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FET DEVICES AND APPLICATIONS

Chairman: Joseph A. Calviello—Eaton Corporation/AIL

Session Abstract: The topics that will be covered in this session range from FET design and processing issues to FET-based circuit design, modelling and implementation. The effect of co-implantation of p-type dopants on MESFET rf performance will be described, followed by a presentation of a novel self-aligned gate process for submicron gate length power FETs. The implementation of a GaInAs MISFET mixer will conclude the discussion on devices and processing. Presentations on the design of a distributed FET mixer circuit and of a straightforward CAD procedure for a FET dielectric resonant oscillator will conclude the technical presentation on this session.

**2:00 p.m.–3:30 p.m., Thursday, June 15, 1989
Terrace Theater**